

MOSFET

OptiMOS™ Power-MOSFET, 30 V

Features

- Optimized for high performance buck converter
- 175°C rated
- Very low on-resistance $R_{DS(on)}$ @ $V_{GS}=4.5\text{ V}$
- 100% avalanche tested
- Superior thermal resistance
- N-channel
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

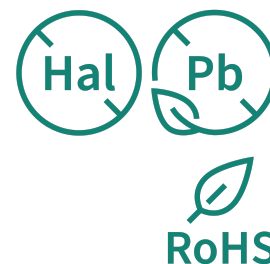
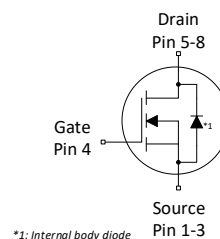
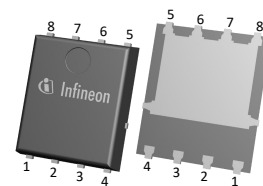
Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	30	V
$R_{DS(on),max}$	1.1	mΩ
I_D	240	A
Q_{OSS}	40	nC
$Q_G(0V..10V)$	72	nC

PG-TDSON-8



Type/Ordering Code	Package	Marking	Related Links
BSC011N03LS	PG-TDSON-8	011N03LS	-



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1 Maximum ratings

unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	240	A	$V_{GS}=10\text{ V}, T_C=25\text{ °C}$ $V_{GS}=10\text{ V}, T_C=100\text{ °C}$ $V_{GS}=4.5\text{ V}, T_C=25\text{ °C}$ $V_{GS}=4.5\text{ V}, T_C=100\text{ °C}$ $V_{GS}=10\text{ V}, T_A=25\text{ °C}, R_{thJA}=50\text{ K/W}^2)$
				170		
				213		
				150		
				39		
Pulsed drain current ³⁾	$I_{D,pulse}$	-	-	960	A	$T_C=25\text{ °C}$
Avalanche current, single pulse ⁴⁾	I_{AS}	-	-	50	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse	E_{AS}	-	-	190	mJ	$I_D=50\text{ A}, R_{GS}=25\text{ }\Omega$
Gate source voltage ⁵⁾	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	115	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}, R_{thJA}=50\text{ K/W}^2)$
				3.0		
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	-

¹⁾ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature at 25°C. For higher case temperature please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ See Diagram 3 for more detailed information

⁴⁾ See Diagram 13 for more detailed information

⁵⁾ The negative rating is for low duty cycle pulse occurrence. No continuous rating is implied

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	1.3	K/W	-
Thermal resistance, junction - case, top	R_{thJC}	-	-	20	K/W	-
Device on PCB, 6 cm ² cooling area ⁶⁾	R_{thJA}	-	-	50	K/W	-

⁶⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

3 Electrical characteristics

unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	-	-	V	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	1.2	-	2	V	$V_{DS}=V_{GS}, I_D=250\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=30\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ }^\circ\text{C}$ $V_{DS}=30\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ }^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	10	100	nA	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	1.1 0.9	1.4 1.1	m Ω	$V_{GS}=4.5\text{ V}, I_D=30\text{ A}$ $V_{GS}=10\text{ V}, I_D=30\text{ A}$
Gate resistance ⁷⁾	R_G	0.3	0.6	1.2	Ω	-
Transconductance	g_{fs}	85	170	-	S	$ V_{DS} >2 I_D R_{DS(on)max}, I_D=30\text{ A}$

⁷⁾ Defined by design. Not subject to production test

Table 5 Dynamic characteristics ⁸⁾

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	4700	6251	pF	$V_{GS}=0\text{ V}, V_{DS}=15\text{ V}, f=1\text{ MHz}$
Output capacitance	C_{oss}	-	1500	1995	pF	$V_{GS}=0\text{ V}, V_{DS}=15\text{ V}, f=1\text{ MHz}$
Reverse transfer capacitance	C_{rss}	-	220	-	pF	$V_{GS}=0\text{ V}, V_{DS}=15\text{ V}, f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	6.7	-	ns	$V_{DD}=15\text{ V}, V_{GS}=10\text{ V}, I_D=30\text{ A},$ $R_{G,ext}=1.6\text{ }\Omega$
Rise time	t_r	-	8.8	-	ns	$V_{DD}=15\text{ V}, V_{GS}=10\text{ V}, I_D=30\text{ A},$ $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	37	-	ns	$V_{DD}=15\text{ V}, V_{GS}=10\text{ V}, I_D=30\text{ A},$ $R_{G,ext}=1.6\text{ }\Omega$
Fall time	t_f	-	6.2	-	ns	$V_{DD}=15\text{ V}, V_{GS}=10\text{ V}, I_D=30\text{ A},$ $R_{G,ext}=1.6\text{ }\Omega$

⁸⁾ Defined by design. Not subject to production test

Table 6 Gate charge characteristics ⁹⁾

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	11	15	nC	$V_{DD}=15\text{ V}, I_D=30\text{ A}, V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	7.5	-	nC	$V_{DD}=15\text{ V}, I_D=30\text{ A}, V_{GS}=0\text{ to }4.5\text{ V}$
Gate to drain charge	Q_{gd}	-	10.3	13	nC	$V_{DD}=15\text{ V}, I_D=30\text{ A}, V_{GS}=0\text{ to }4.5\text{ V}$

Table 6 Gate charge characteristics ⁹⁾

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Switching charge	Q_{sw}	-	14	-	nC	$V_{DD}=15\text{ V}$, $I_D=30\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge total	Q_g	-	36	48	nC	$V_{DD}=15\text{ V}$, $I_D=30\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	2.4	-	V	$V_{DD}=15\text{ V}$, $I_D=30\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge total	Q_g	-	72	96	nC	$V_{DD}=15\text{ V}$, $I_D=30\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	29	-	nC	$V_{DS}=0.1\text{ V}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Output charge	Q_{oss}	-	40	53	nC	$V_{DD}=15\text{ V}$, $V_{GS}=0\text{ V}$

⁹⁾ See "Gate charge waveforms" for parameter definition. Defined by design. Not subject to production test

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	115	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	960	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.8	1	V	$V_{GS}=0\text{ V}$, $I_F=30\text{ A}$, $T_J=25\text{ °C}$
Reverse recovery charge ¹⁰⁾	Q_{rr}	-	20	-	nC	$V_R=15\text{ V}$, $I_F=I_S$, $di_F/dt=400\text{ A}/\mu\text{s}$

¹⁰⁾ Defined by design. Not subject to production test

4 Electrical characteristics diagrams

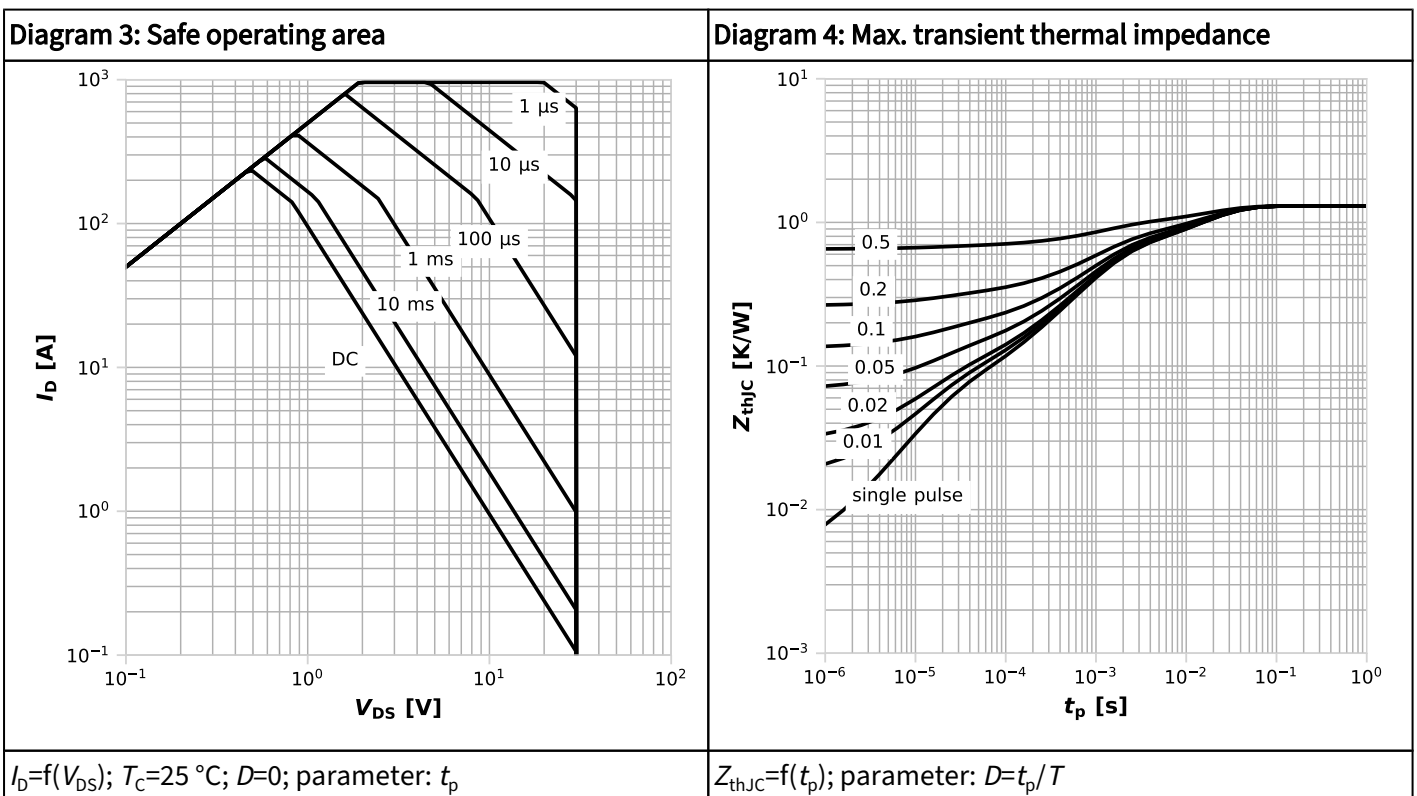
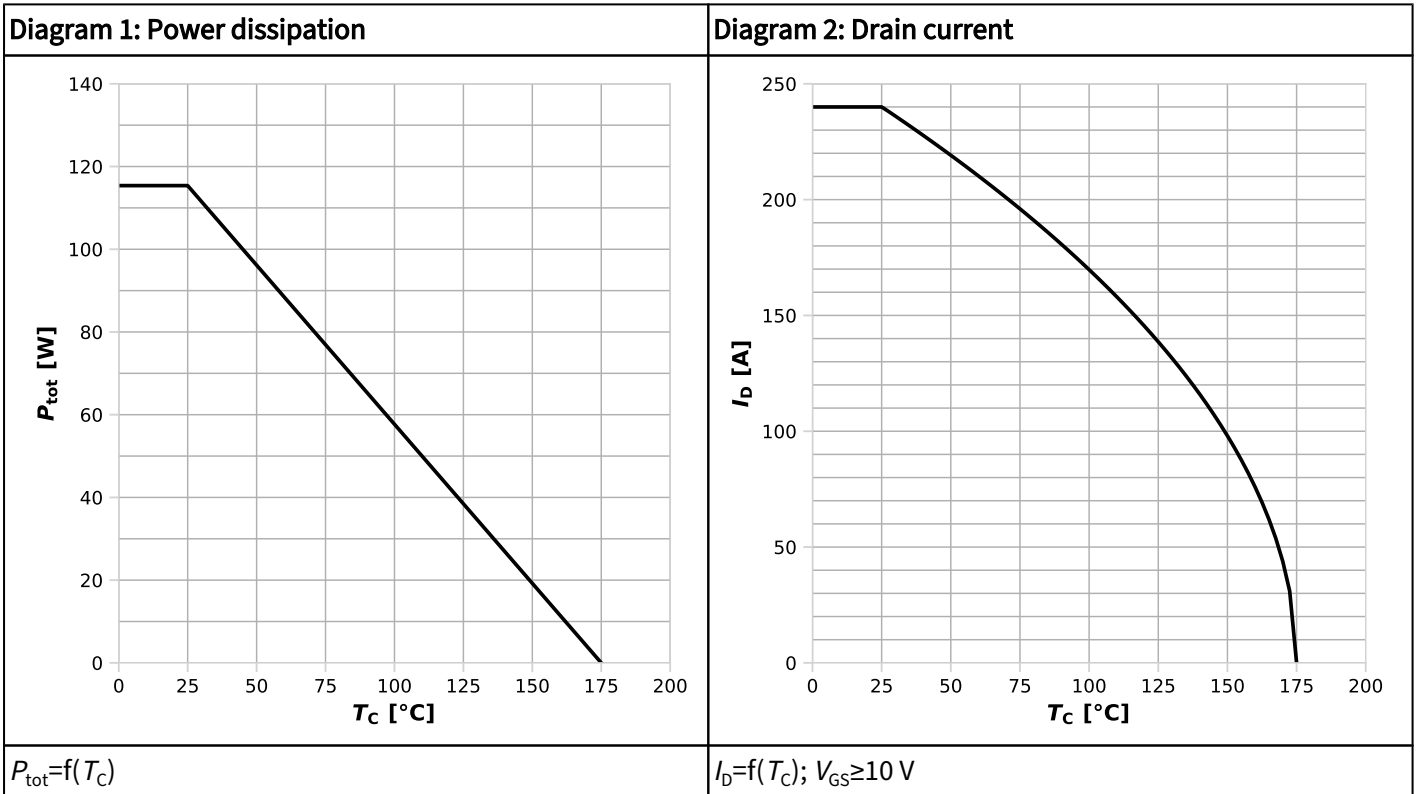
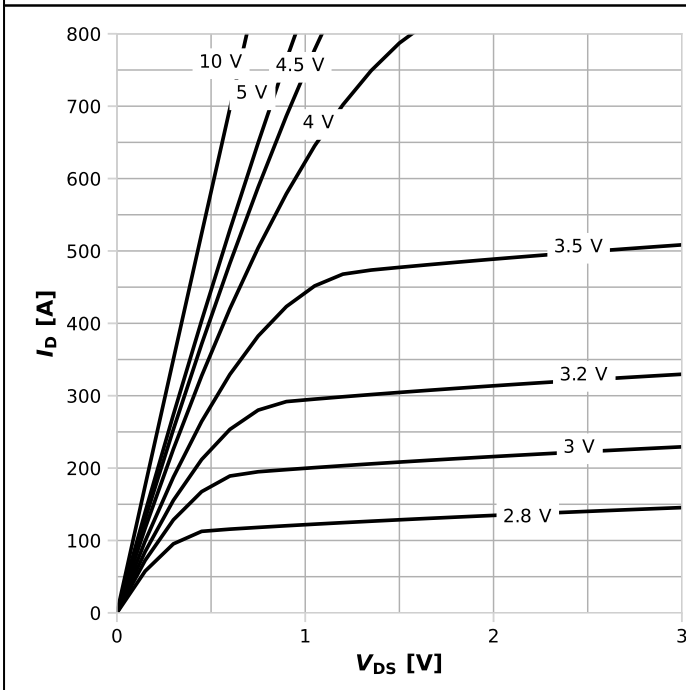
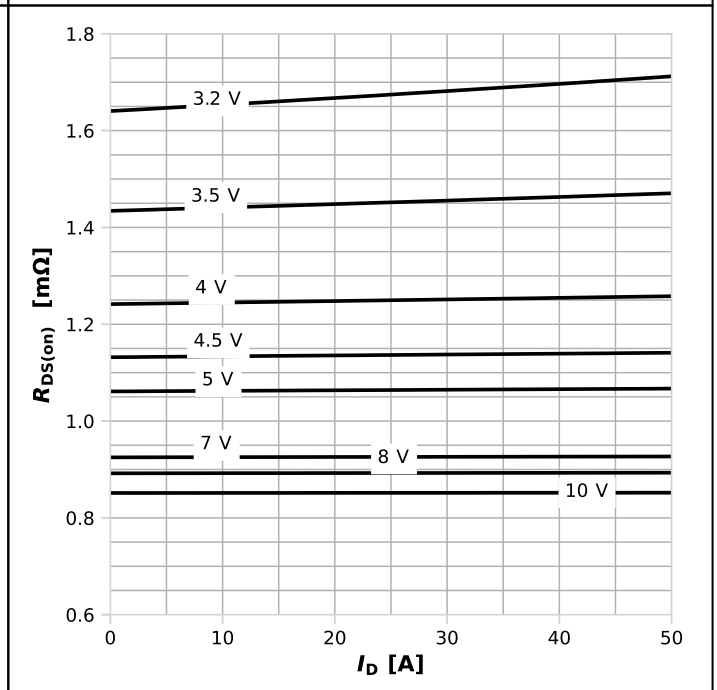


Diagram 5: Typ. output characteristics



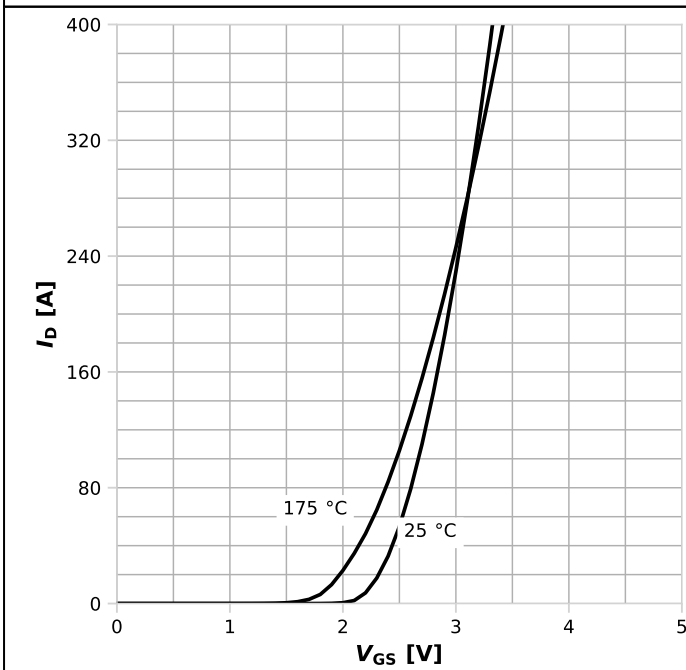
$I_D = f(V_{DS}); T_j = 25\text{ °C}; \text{parameter: } V_{GS}$

Diagram 6: Typ. drain-source on resistance



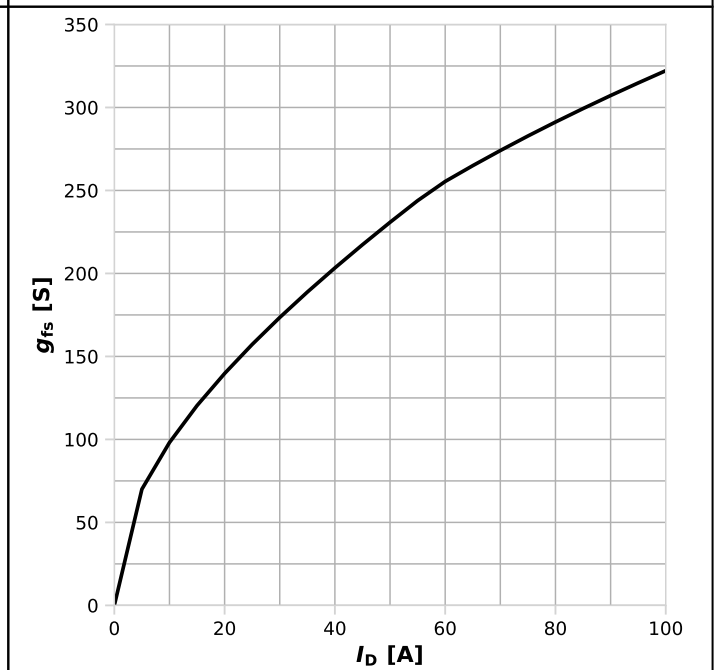
$R_{DS(on)} = f(I_D); T_j = 25\text{ °C}; \text{parameter: } V_{GS}$

Diagram 7: Typ. transfer characteristics



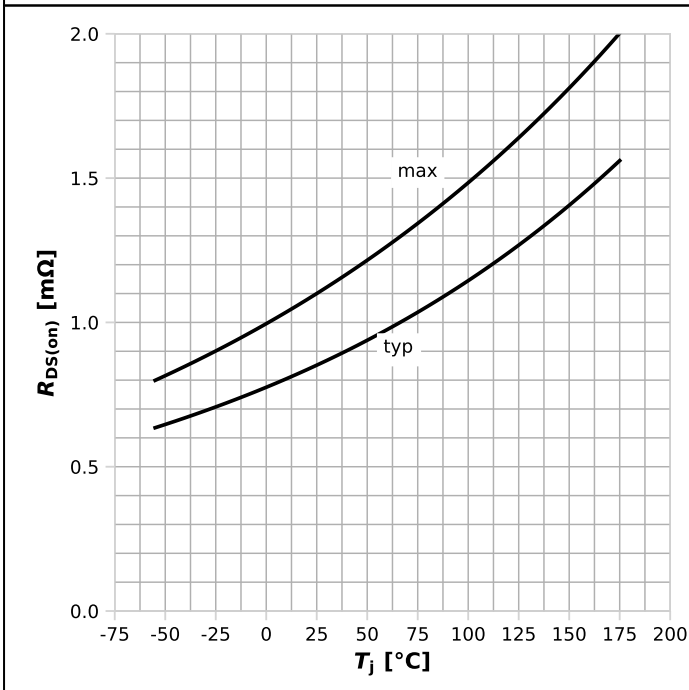
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}; \text{parameter: } T_j$

Diagram 8: Typ. forward transconductance



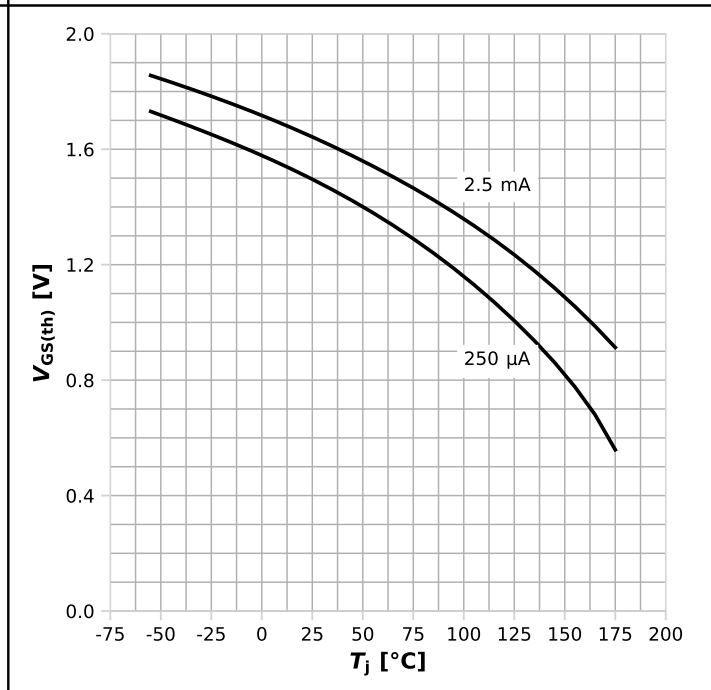
$g_{fs} = f(I_D); T_j = 25\text{ °C}$

Diagram 9: Drain-source on-state resistance



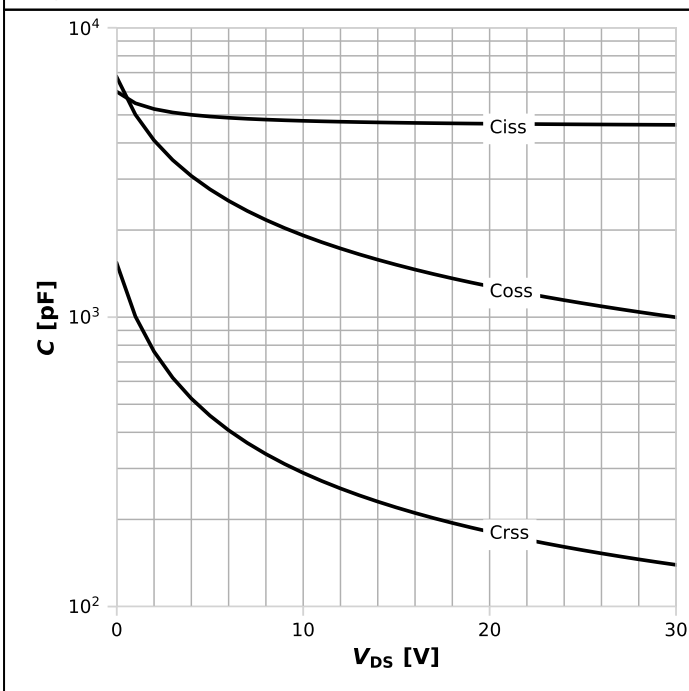
$R_{DS(on)} = f(T_j); I_D = 30 \text{ A}; V_{GS} = 10 \text{ V}$

Diagram 10: Typ. gate threshold voltage



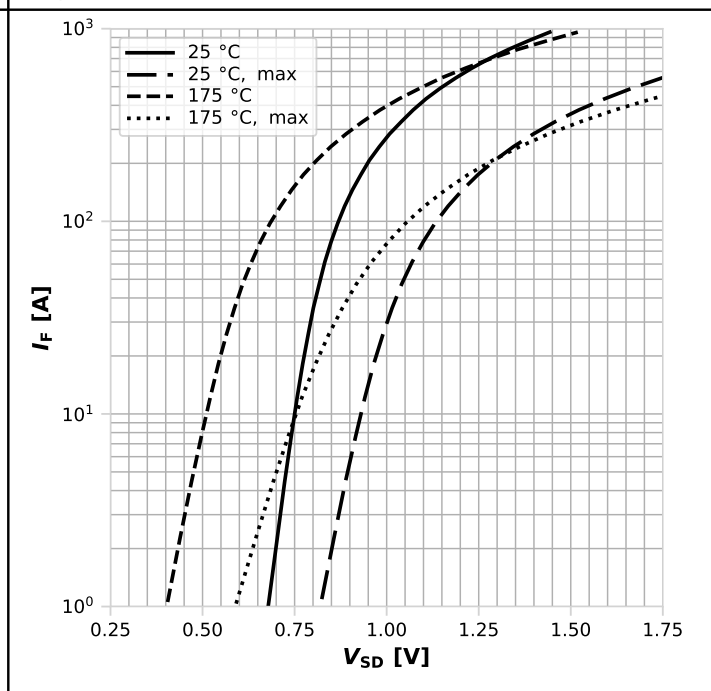
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = 250 \mu\text{A}$

Diagram 11: Typ. capacitances



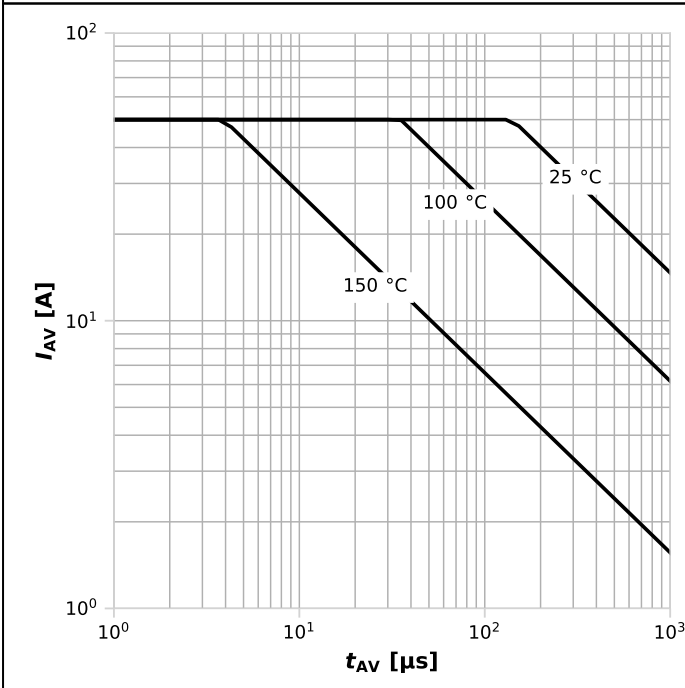
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

Diagram 12: Forward characteristics of reverse diode



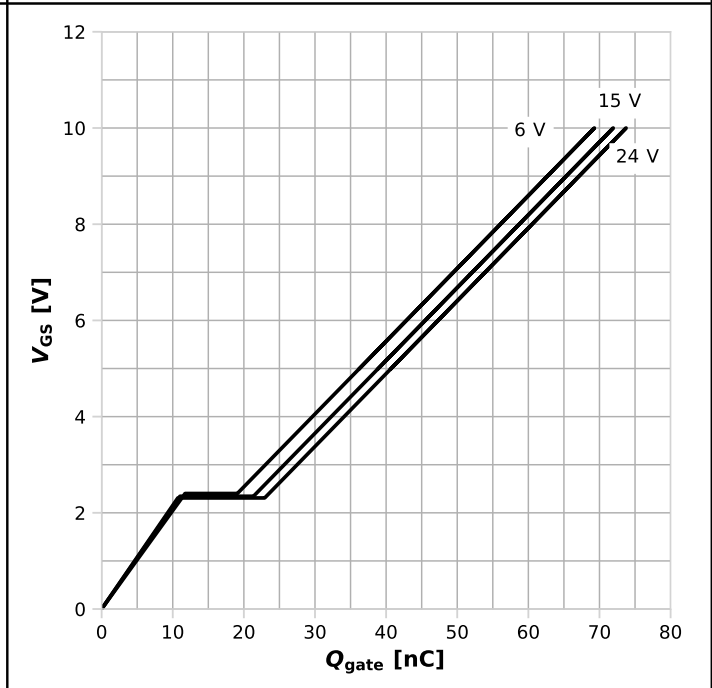
$I_F = f(V_{SD}); \text{parameter: } T_j$

Diagram 13: Avalanche characteristics



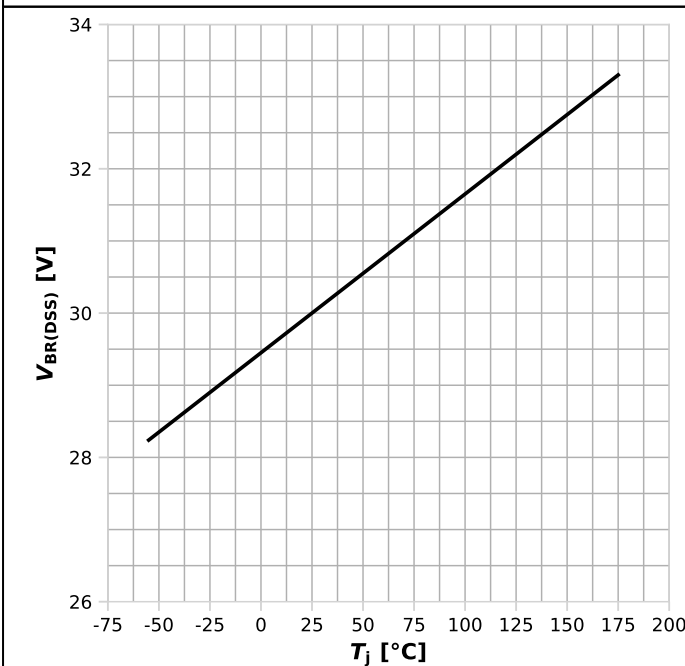
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



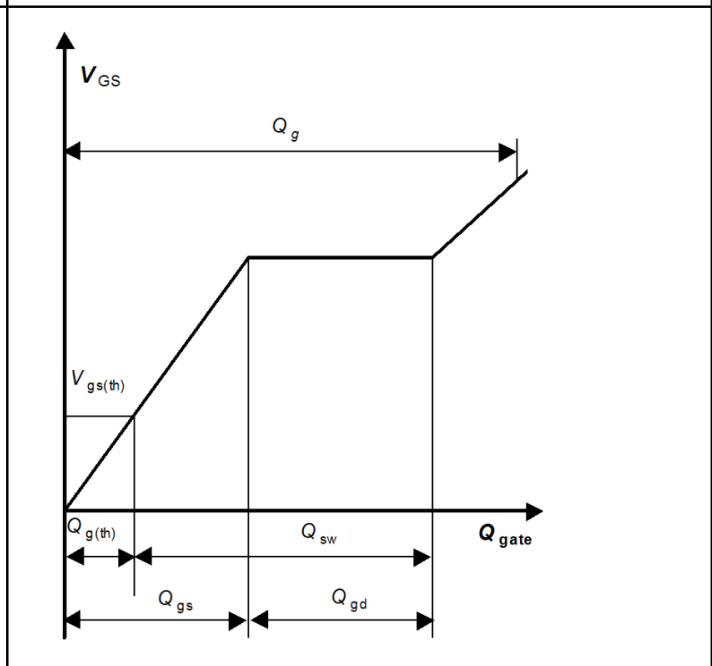
$V_{GS}=f(Q_{gate}); I_D=30 \text{ A pulsed}$; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage



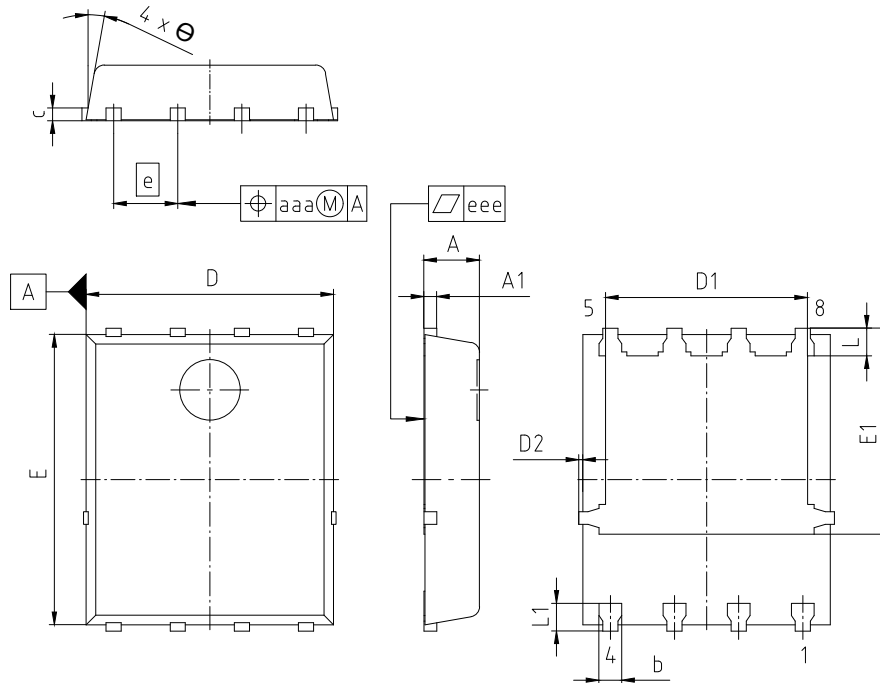
$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

Gate charge waveforms



-

5 Package Outlines



PACKAGE - GROUP NUMBER: PG-TDSON-8-U08		
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	0.90	1.20
A1	0.15	0.35
b	0.34	0.54
c	0.15	0.35
D	4.80	5.35
D1	3.90	4.40
D2	0.00	0.22
E	5.70	6.10
E1	4.03	4.25
e	1.27	
L	0.45	0.72
L1	0.45	0.71
aaa	0.25	
eee	0.05	
θ	8°	12°

- 1) EXCLUDING MOLD FLASH
- 2) REMOVAL ON MOLD GATE
INTRUSION 0.1 MM
PROTRUSION 0.1 MM
- 3) ALL METAL SURFACES ARE PLATED,
EXCEPT AREA OF CUT

Figure 1 Outline PG-TDSON-8, dimensions in mm

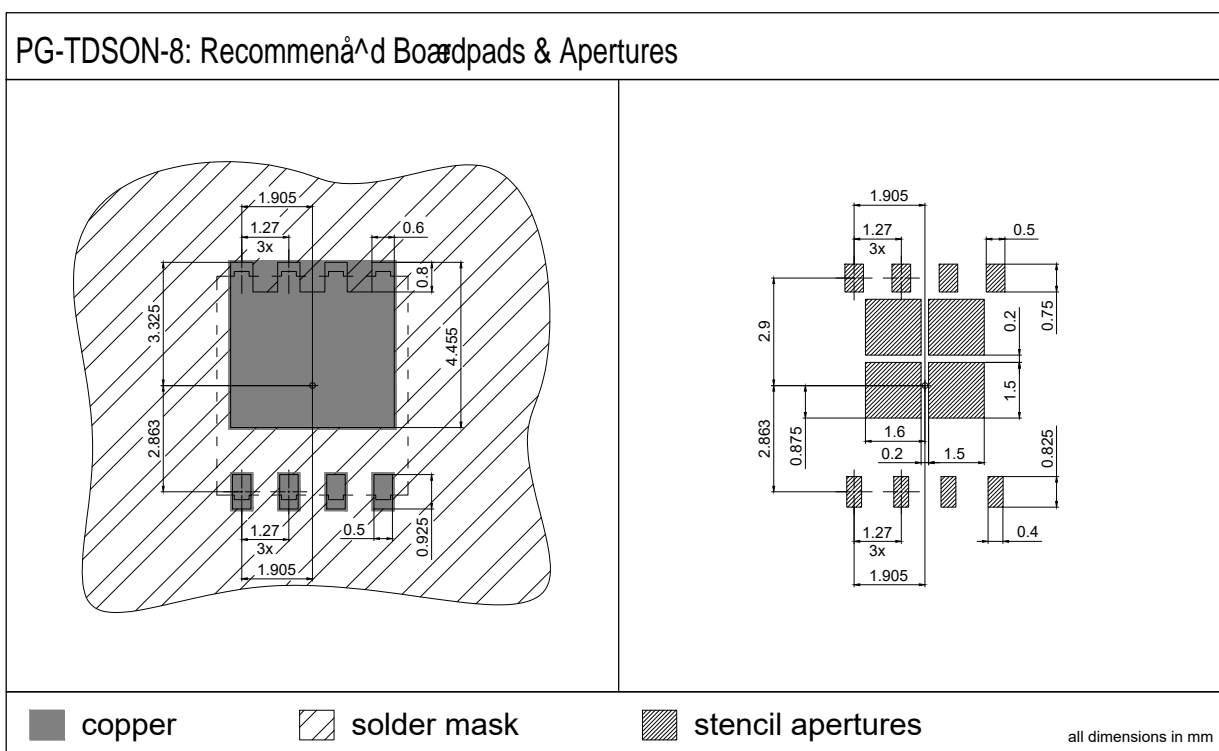


Figure 2 Outline PG-TDSON-8, dimensions in mm

Revision History

BSC011N03LS

Revision 2024-06-04, Rev. 2.6

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.3	2019-10-01	Update package drawings
2.4	2020-03-13	Update current rating
2.5	2023-03-28	Update footnotes and package outline drawings
2.6	2024-06-04	Upgrade Operating and storage temperature max to 175°C. Update drawings in section 5 Package Outlines. Production validation added on page1.Updated foot notes.

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